

RJF0614JSP

60V, 1.5A N Channel Thermal FET Power Switching

R07DS1251EJ0100 Rev.1.00 Jun 16, 2015

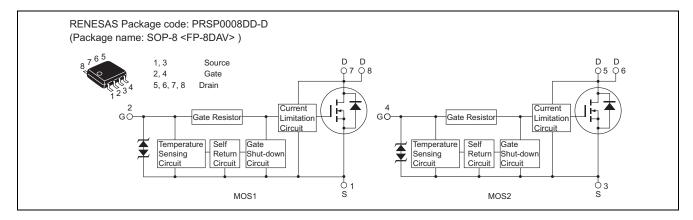
Description

This FET has the over temperature shut-down capability sensing to the junction temperature. This FET has the built-in over temperature shut-down circuit in the gate area. And this circuit operation to shut-down the gate voltage in case of high junction temperature like applying over power consumption, over current etc..

Features

- Logic level operation (5 to 6 V Gate drive).
- Built-in the over temperature shut-down circuit.
- High endurance capability against to the short circuit.
- Temperature hysteresis type.
- High density mounting
- Power supply voltage applies 12 V and 24 V.
- AEC-Q101 Compliant

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{ extsf{DSS}}$	60	V
Gate to source voltage	V_{GSS}	16	V
Gate to source voltage	V_{GSS}	-2.5	V
Drain current	I _D Note4	1.5	Α
Body-drain diode reverse drain current	I_{DR}	1.5	Α
Avalanche current	I _{AP} Note 3	0.9	Α
Avalanche energy	E _{AR} Note 3	69.4	mJ
Channel dissipation	Pch Note 1	2	W
Channel dissipation	Pch Note 2	3	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	−55 to +150	°C

Notes: 1. 1 Drive operation: When using the glass epoxy board (FR4 $40 \times 40 \times 1.6$ mm), PW ≤ 10 s

- 2. 2 Drive operation: When using the glass epoxy board (FR4 $40 \times 40 \times 1.6$ mm), PW ≤ 10 s
- 3. Tch = 25°C, Rg \geq 50 Ω , L = 100 mH
- 4. It provides by the current limitation lower bound value.

Typical Operation Characteristics

 $(Ta = 25^{\circ}C)$

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Input voltage	V _{IH}	3.5	_	_	V	
	V_{IL}	_	_	1.2	V	
Input current	I _{IH1}	_	_	100	μА	Vi = 8 V, V _{DS} = 0
(Gate non shut down)	I _{IH2}	_	_	50	μА	Vi = 3.5 V, V _{DS} = 0
	I _{IL}	_	_	1	μА	Vi = 1.2 V, V _{DS} = 0
Input current	I _{IH(sd)1}	_	0.8	_	mA	Vi = 8 V, V _{DS} = 0
(Gate shut down)	I _{IH(sd)2}	_	0.35	_	mA	Vi = 3.5 V, V _{DS} = 0
Shut down temperature	Tsd	_	175	_	°C	Channel temperature
Return temperature	Thr	_	120	_	°C	Channel temperature
Gate operation voltage	Vop	3.5	_	12	V	
Drain current (Current limitation value)	I _{D limit}	1.5	_	_	А	V _{GS} = 5 V, V _{DS} = 10 V Note 5

Notes: 5. Pulse test

Electrical Characteristics

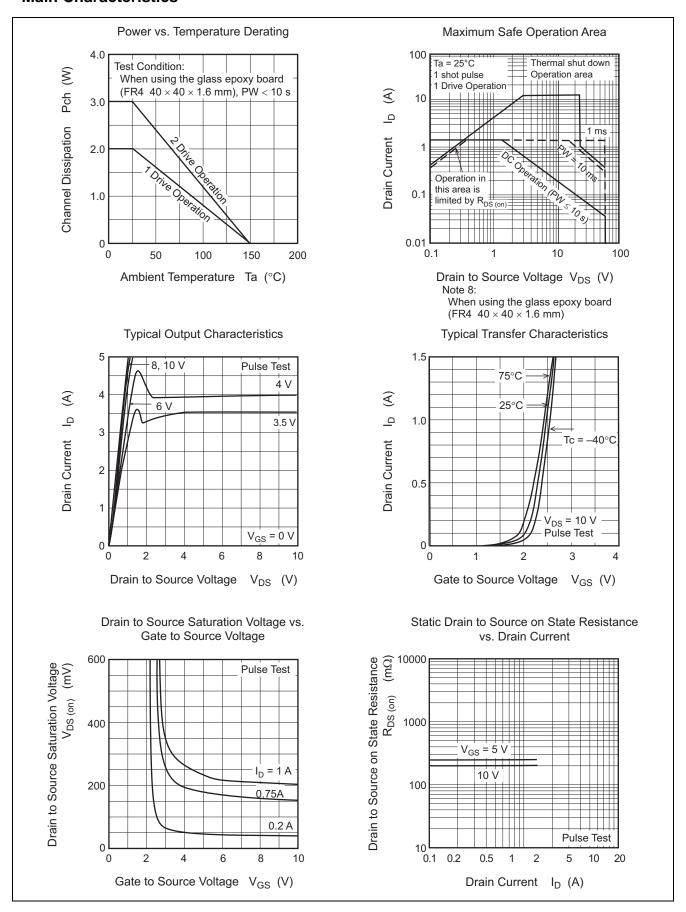
 $(Ta = 25^{\circ}C)$

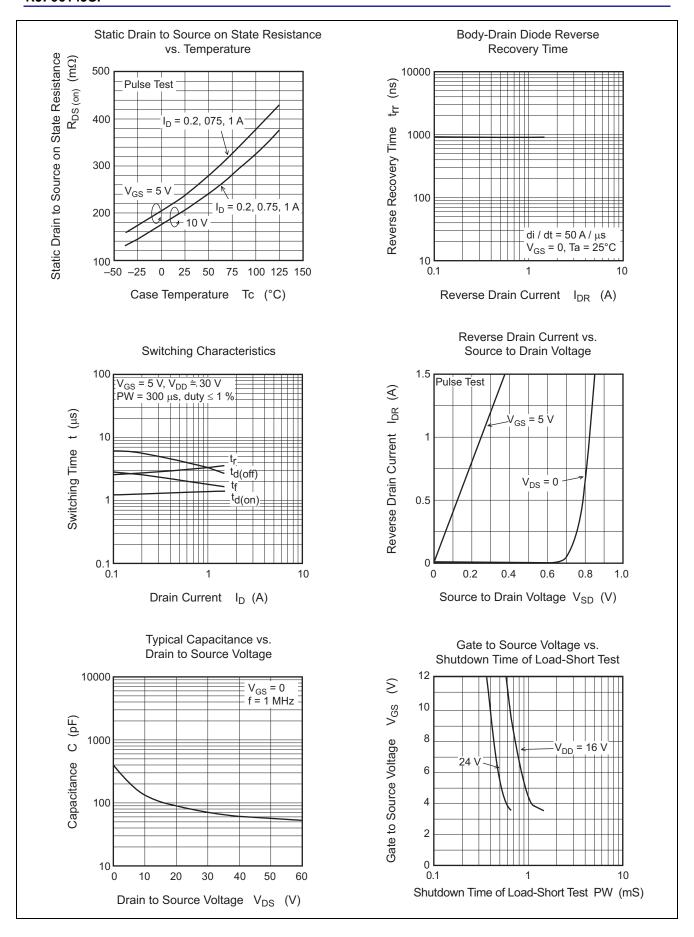
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain current	I _{D1}	_	_	5.5	Α	V _{GS} = 3.5 V, V _{DS} = 10 V Note 6
	I _{D2}	_	_	10	mA	V _{GS} = 1.2 V, V _{DS} =10 V
	I _{D3}	1.5	_	_	Α	V _{GS} = 5 V, V _{DS} = 10 V Note 6
Drain to source breakdown voltage	V _{(BR)DSS}	60	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	V _{(BR)GSS}	16		_	V	$I_G = 800 \ \mu A, \ V_{DS} = 0$
	V _{(BR)GSS}	-2.5		_	V	$I_G = -100 \mu\text{A}, V_{DS} = 0$
Gate to source leak current	I _{GSS1}			100	μΑ	$V_{GS} = 8 \text{ V}, V_{DS} = 0$
	I _{GSS2}			50	μΑ	$V_{GS} = 3.5 \text{ V}, V_{DS} = 0$
	Igss ₃			1	μΑ	$V_{GS} = 1.2 \text{ V}, V_{DS} = 0$
	I _{GSS4}	_		-100	μΑ	$V_{GS} = -2.4 \text{ V}, V_{DS} = 0$
Input current (shut down)	IGS(OP)1	_	0.8	_	mA	$V_{GS} = 8 \text{ V}, V_{DS} = 0$
	I _{GS(OP)2}	_	0.35	_	mA	$V_{GS} = 3.5 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	IDSS	_	_	10	μΑ	$V_{DS} = 32 \text{ V}, V_{GS} = 0,$
						Ta = 125°C
Gate to source cutoff voltage	V _{GS(off)}	1.1	_	2.1	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static drain to source on state	R _{DS(on)}	_	238	297	mΩ	$I_D = 0.75 \text{ A}, V_{GS} = 5 \text{ V}^{\text{Note 6}}$
resistance	R _{DS(on)}	_	201	250	mΩ	$I_D = 0.75 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note 6}}$
Output capacitance	Coss	_	130	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0, f = 1MHz$
Turn-on delay time	t _{d(on)}	_	1.4	_	μS	$I_D = 0.75 \text{ A}, V_{GS} = 5 \text{ V},$
Rise time	tr	_	3.1	_	μS	$R_L = 40 \Omega$
Turn-off delay time	t _{d(off)}	_	3.6	_	μS	
Fall time	t _f		1.9	_	μS	
Body-drain diode forward voltage	V_{DF}	_	0.8	_	V	I _F = 1.5 A, V _{GS} = 0
Body-drain diode reverse recovery	t _{rr}	_	910	_	ns	$I_F = 1.5 \text{ A}, V_{GS} = 0$
time						di _F /dt = 50 A/μs
Over load shut down	t _{os1}	_	0.94	_	ms	$V_{GS} = 5 \text{ V}, V_{DD} = 16 \text{ V}$
operation time Note 7	t _{os2}	_	0.53	_	ms	$V_{GS} = 5 \text{ V}, V_{DD} = 24 \text{ V}$

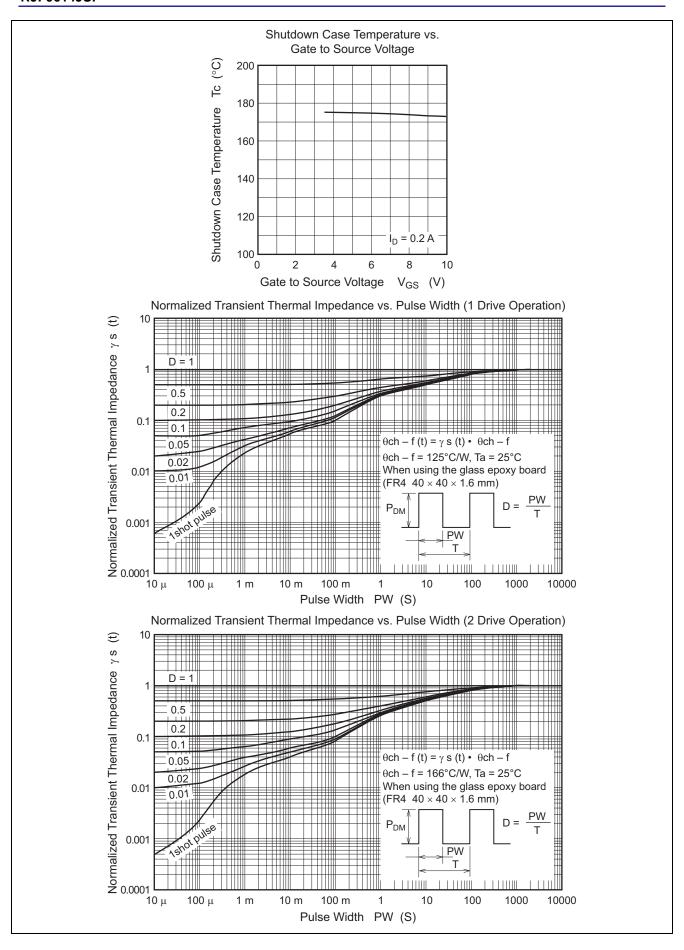
Notes: 6. Pulse test

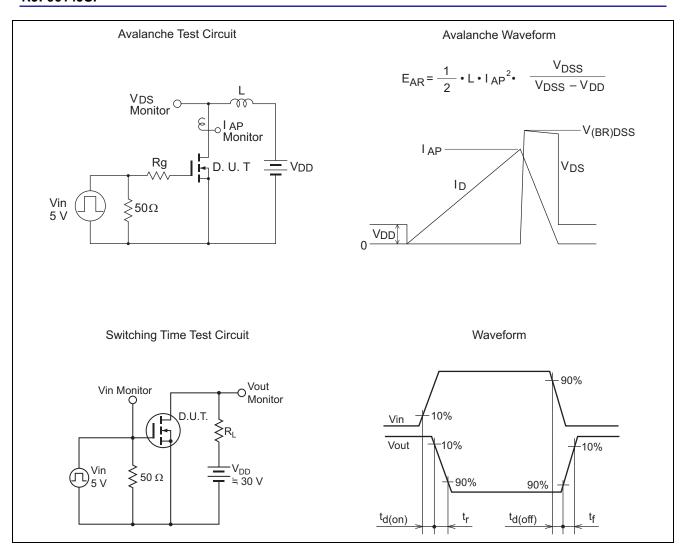
7. Including the junction temperature rise of the over loaded condition.

Main Characteristics

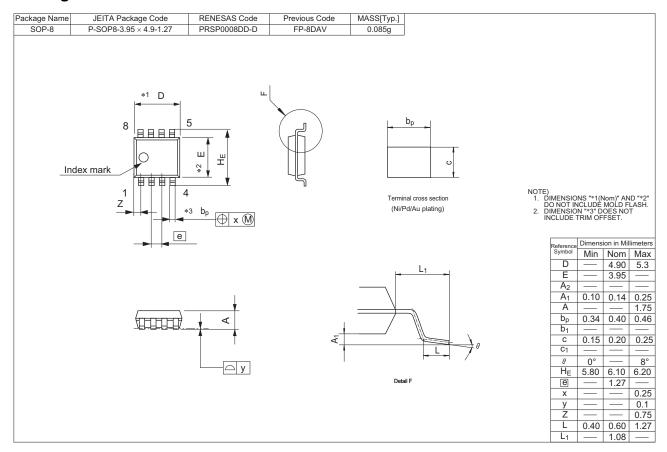








Package Dimensions



Ordering Information

Orderable Part Number	Quantity	Shipping Container
RJF0614JSP-00#J0	2500 pcs	Taping (Reel)

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